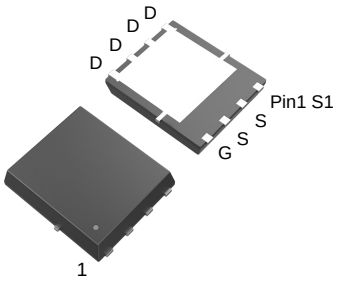
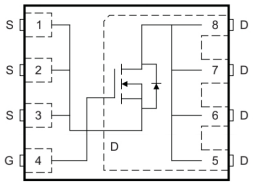
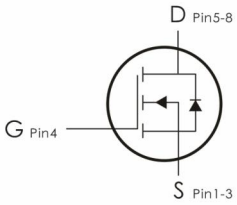
Description：

This N-Channel MOSFET uses advanced SGT technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.







Features：

1) V_{DS}=60V,I_D=120A,$R_{DS(ON)}$<3.5mΩ @V_{GS}=10V（Typ：2.6mΩ）
2) Low gate charge.
3) Green device available.
4) Advanced high cell denity SGT technology for ultra low $R_{DS(ON)}$.
5) Excellent package for good heat dissipation.
6) MSL3

Package Marking and Ordering Information：

Part NO.	Marking	Package	Packing
NE3R5T3G	E3R5T3	DFN5*6-8	5000 pcs/Reel

Absolute Maximum Ratings：(T_C=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current[1]	120	A
	Continuous Drain Current-T_C=100℃[1]	84	
I_{DM}	Pulsed Drain Current [2]	360	
P_D	Power Dissipation	96	W
E_{AS}	Single pulse avalanche energy[3]	177	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	℃

Thermal Characteristics：

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance,Junction to Case	1.3	℃/W

Electrical Characteristics: (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	60	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS}=0V, V_{DS}=60V	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V, V_{DS}=0A	---	---	±100	nA
On Characteristics (Note3)						
$V_{GS(th)}$	Gate-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	1	---	2	V
$R_{DS(ON)}$	Drain-Source On Resistance [4]	V_{GS}=10V,I_D=20A	---	2.6	3.5	mΩ
		V_{GS}=4.5V,I_D=10A	---	3.4	5	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=25V, V_{GS}=0V, f=1MHz	---	3500	---	pF
C_{oss}	Output Capacitance		---	1176	--	
C_{rss}	Reverse Transfer Capacitance		---	42	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DS}=30V, I_D=15A, R_G=3Ω,V_{GS}=10V	---	20	---	ns
t_r	Rise Time		---	82	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	105	---	ns
t_f	Fall Time		---	25	---	ns
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=30V, I_D=30A	---	45	---	nC
Q_{gs}	Gate-Source Charge		---	10	---	nC
Q_{gd}	Gate-Drain “Miller” Charge		---	15	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	V_{GS}=0V, I_{SD}=30A	---	---	1.2	V
I_S	Continuous Drain Curren	V_D=V_G=0V	---	---	120	A
I_{SM}	Pulsed Drain Current		---	---	360	A
Trr	Reverse Recovery Time	I_F=20A,T_J=25℃ dI/dt=100A/us	---	11	---	ns
Qrr	Reverse Recovery Charge		---	2.5	---	nC

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. EAS condition : TJ=25℃,VDD=30V,V_G=10V,L=0.1mH
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Characteristics: (T_C=25℃ unless otherwise noted)

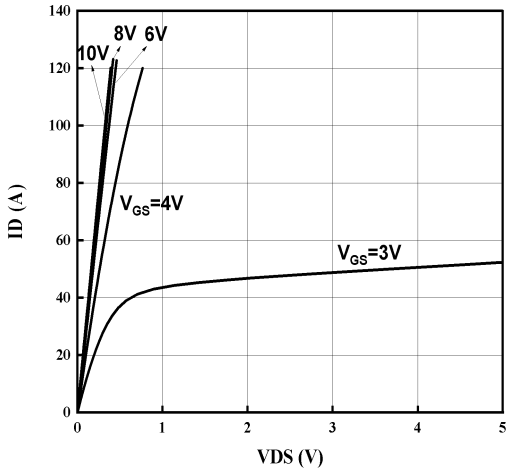


Fig1. Typical Output Characteristics

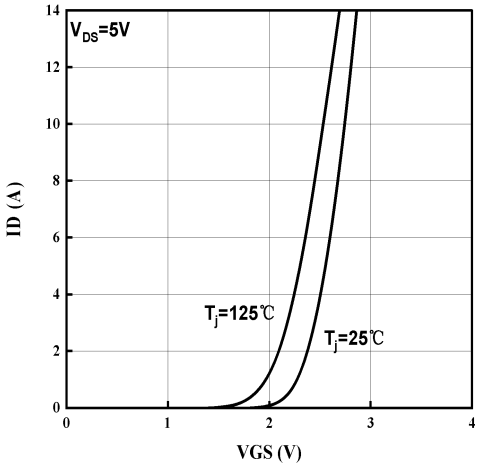


Fig2. Typical Transfer Characteristics

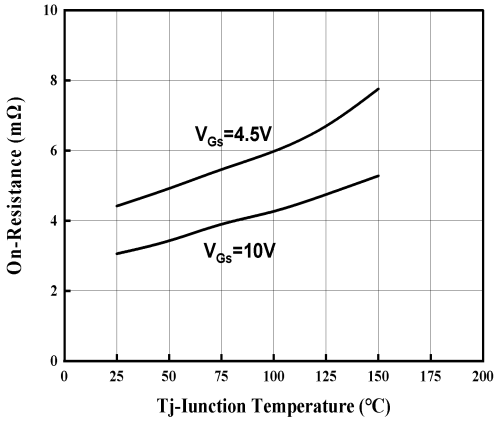


Fig3. On-Resistance Vs. Temperature

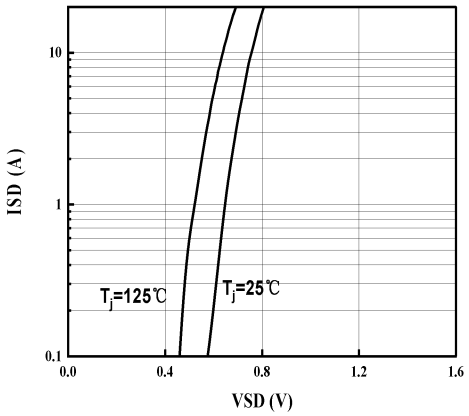


Fig4. Typical Source-Drain Diode Forward Voltage

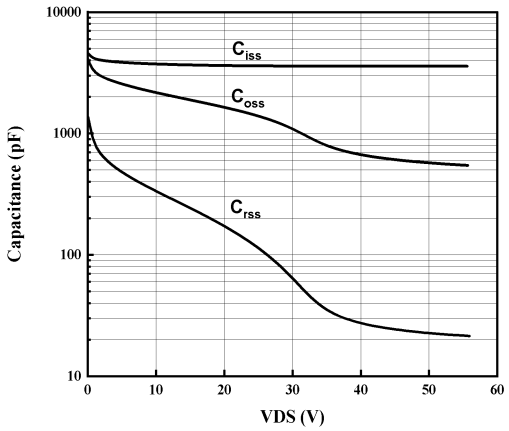


Fig5. Typical.Capacitance

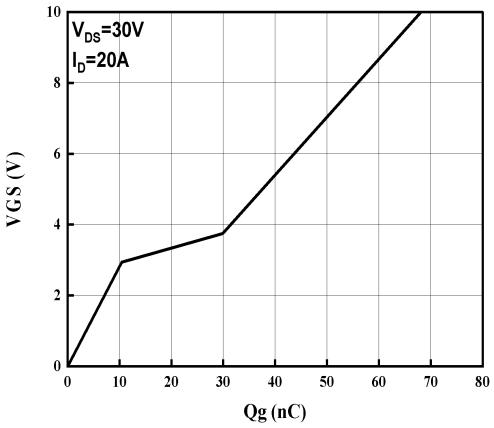


Fig6. Typical.Gate Charge

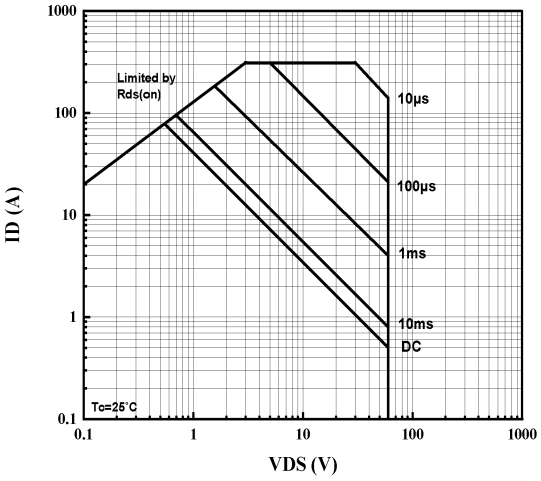


Fig7. Safe Operating Area

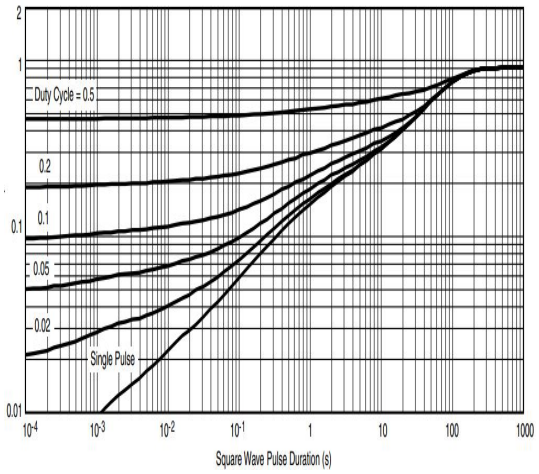
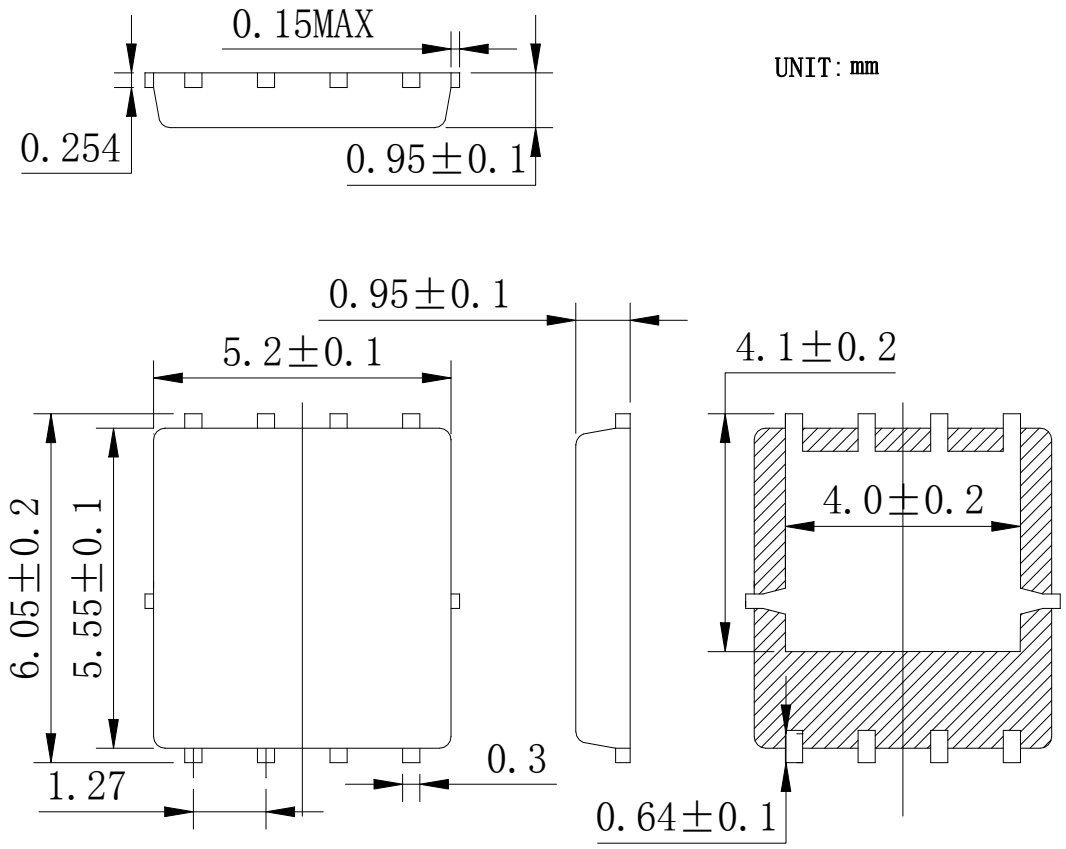


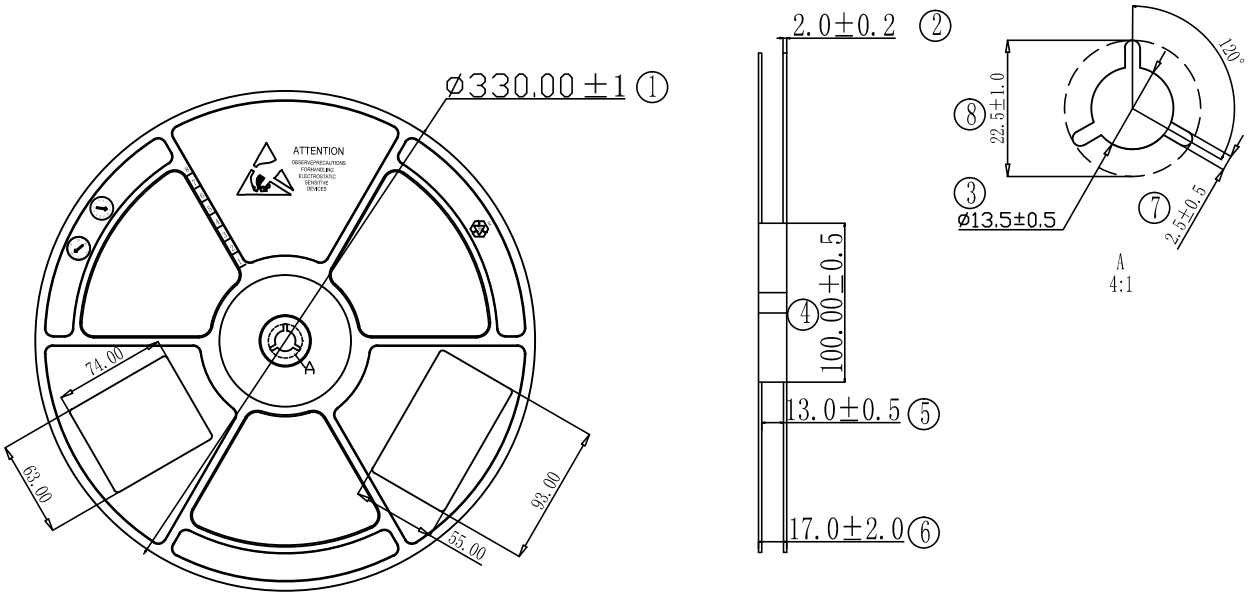
Fig8. Normalized transient thermal impedance

DFN5×6-8 Package Information：

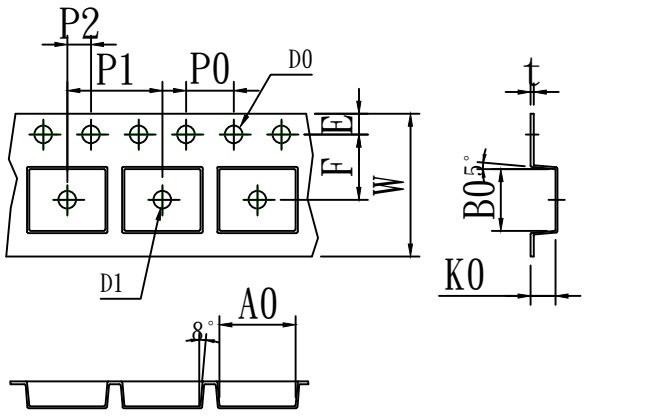


Tape & Reel Information

Dimensions in mm



Symbol	A0	B0	K0	D0	D1	P0	P1	10*P0
Spec	6.15±0.10	5.40±0.10	1.30±0.10	1.55±0.10	1.55±0.10	4.00±0.10	8.00±0.10	40.00±0.10
Symbol	W	E	F	P2	t			
Spec	12.00±0.10	1.75±0.10	5.50±0.10	2.00±0.10	0.20±0.05			



Marking Information：

①. Doingter LOGO

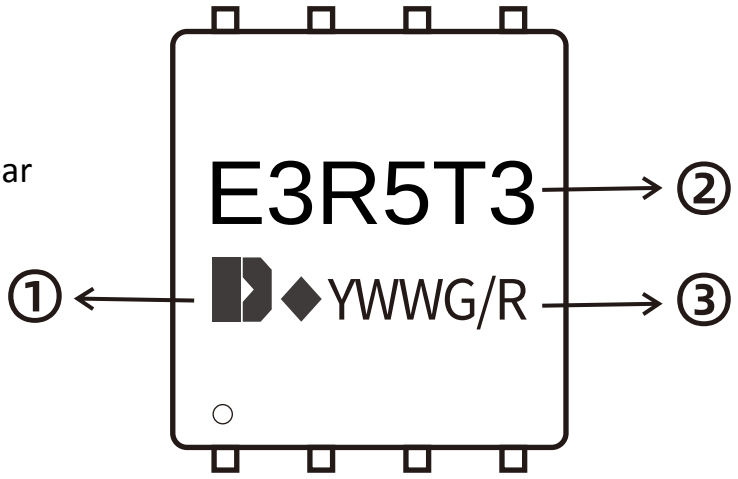
②. Part NO.

③. Date Code(YWWG / R)

Y：Year Code，last digit of the year

WW：Week Code(01-53)

G/R：G(Green) /R(Lead Free)



Previous Version

Version	Date	Subjects (major changes since last revision)
1.1	2025-06-06	Release of final version

Attention：

- Information furnished in this document is believed to be accurate and reliable. However, Shenzhen Doingter Semiconductor Co.,Ltd. assumes noresponsibility for the consequences of use without consideration for such information nor use beyond it.
- Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Shenzhen Doingter complies with the agreement. Products and information provided in this document have no infringement of patents.
- Shenzhen Doingter assumes noresponsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied. Is a registered trademark of Shenzhen Doingter Semiconductor Co., Ltd. Copyright © 2013 Shenzhen DoingterSemiconductor Co.,Ltd. Printed All rights reserved.